# **Small Signal MOSFET**

20 V, 915 mA, Single N–Channel with ESD Protection, SC–75 and SC–89

# Features

- Low R<sub>DS(on)</sub> Improving System Efficiency
- Low Threshold Voltage, 1.5 V Rated
- ESD Protected Gate
- Pb–Free Packages are Available

# Applications

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Portables like Cell Phones, PDAs, Digital Cameras, Pagers, etc.

# **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise stated)

Parame	Symbol	Value	Units		
Drain-to-Source Voltage	V <sub>DSS</sub>	20	V		
Gate-to-Source Voltage			V <sub>GS</sub>	±6.0	V
Continuous Drain	Steady	$T_A = 25^{\circ}C$	Ι <sub>D</sub>	915	mA
Current (Note 1)	State	$T_A = 85^{\circ}C$		660	
Power Dissipation (Note 1)	Stea	dy State	P <sub>D</sub>	300	mW
Pulsed Drain Current	t <sub>p</sub> =	=10 μs	I <sub>DM</sub>	1.3	А
Operating Junction and St	T <sub>J</sub> , T <sub>STG</sub>	–55 to 150	°C		
Continuous Source Currer	۱ <sub>S</sub>	280	mA		
Lead Temperature for Solo (1/8" from case for 10 s)	ΤL	260	°C		

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Units
Junction-to-Ambient - Steady State (Note 1)	$R_{\thetaJA}$		°C/W
SC-75 / SOT-416		416	
SC-89		400	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

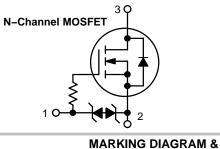
- 1. Surface mounted on FR4 board using 1 in sq pad size
- (Cu area = 1.127 in sq [1 oz] including traces).



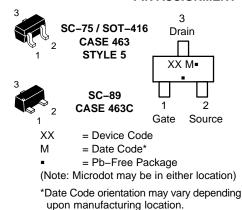
# **ON Semiconductor®**

### http://onsemi.com

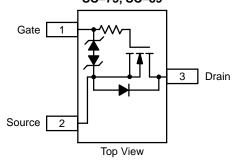
V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> TYP	I <sub>D</sub> MAX
20 V	0.127 Ω @ 4.5 V	
	0.170 Ω @ 2.5 V	915 mA
	0.242 Ω @ 1.8 V	5151114
	0.500 Ω @ 1.5 V	



PIN ASSIGNMENT



SC-75, SC-89



## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** (T<sub>1</sub> = 25°C unless otherwise stated)

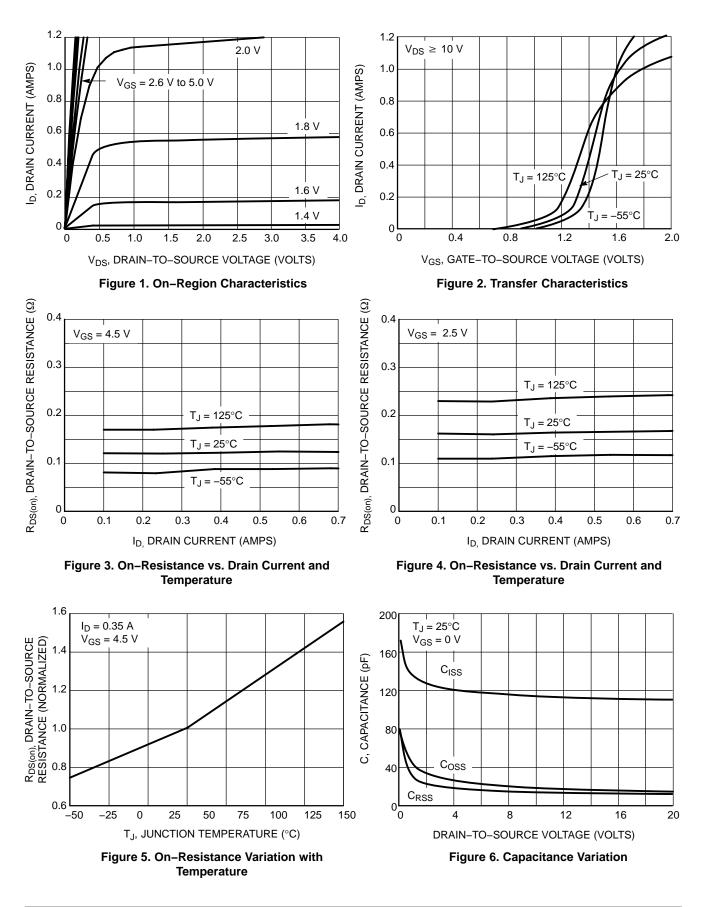
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		20	26		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>				18.4		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V	<sub>DS</sub> = 16 V			100	nA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{G}$	<sub>S</sub> = ±4.5 V			±1.0	μA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_{DS}$	o = 250 μA	0.45	0.76	1.1	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				-2.15		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>E</sub>	<sub>D</sub> = 600 mA		127	230	mΩ
	l f	V <sub>GS</sub> = 2.5 V, I <sub>E</sub>	<sub>D</sub> = 500 mA		170	275	
	$V_{GS}$ = 1.8 V, I <sub>D</sub> = 350 m. $V_{GS}$ = 1.5 V, I <sub>D</sub> = 40 mA		<sub>D</sub> = 350 mA		242	700	-
			<sub>D</sub> = 40 mA		500	9500	
Forward Transconductance	9 <sub>FS</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 400 mA			1.4		S
CHARGES AND CAPACITANCES							
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = 16 V			110		pF
Output Capacitance	C <sub>OSS</sub>				16		7
Reverse Transfer Capacitance	C <sub>RSS</sub>	- 53			12		
Total Gate Charge	Q <sub>G(TOT)</sub>				1.82		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = 4.5 V, V	ν <sub>DS</sub> = 10 V,		0.2		
Gate-to-Source Charge	Q <sub>GS</sub>	$I_D = 0.2$	ŽĂ		0.3		
Gate-to-Drain Charge	Q <sub>GD</sub>				0.42		
SWITCHING CHARACTERISTICS (No	te 3)						
Turn-On Delay Time	t <sub>d(ON)</sub>				3.7		ns
Rise Time	t <sub>r</sub>	$V_{GS}$ = 4.5 V, $V_{DD}$ = 10 V, I <sub>D</sub> = 0.2 A, R <sub>G</sub> = 10 Ω			4.4		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				25		
Fall Time	t <sub>f</sub>				7.6		
DRAIN-SOURCE DIODE CHARACTE	RISTICS						
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V,	$T_J = 25^{\circ}C$		0.67	1.1	V
		I <sub>S</sub> = 200 mA	T <sub>J</sub> = 125°C		0.54		

#### **ORDERING INFORMATION**

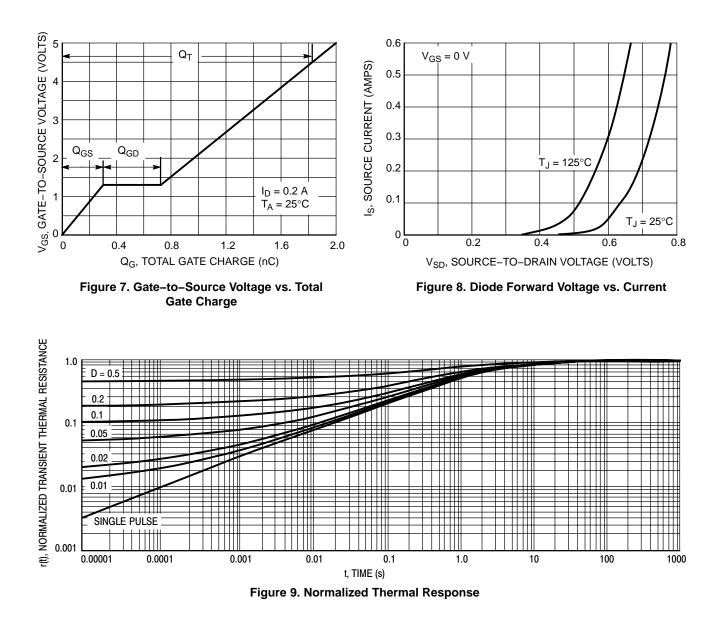
Device	Marking (XX)	Package	Shipping <sup>†</sup>
NTA4153NT1	TR	SC-75 / SOT-416	3000/Tape & Reel
NTA4153NT1G	TR	SC-75 / SOT-416 (Pb-Free)	3000/Tape & Reel
NTE4153NT1G	ТР	SC–89 (Pb–Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **TYPICAL ELECTRICAL CHARACTERISTICS**

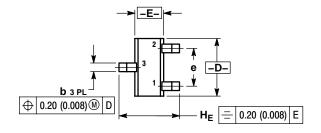


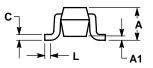
# **TYPICAL ELECTRICAL CHARACTERISTICS**



## PACKAGE DIMENSIONS

SC-75/SOT-416 CASE 463-01 **ISSUE F** 





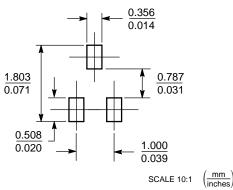
NOTES:

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.70	0.80	0.90	0.027	0.031	0.035	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
b	0.15	0.20	0.30	0.006	0.008	0.012	
С	0.10	0.15	0.25	0.004	0.006	0.010	
D	1.55	1.60	1.65	0.059	0.063	0.067	
Е	0.70	0.80	0.90	0.027	0.031	0.035	
е	1.00 BSC			0	.04 BSC	)	
L	0.10	0.15	0.20	0.004	0.006	0.008	
HE	1.50	1.60	1.70	0.061	0.063	0.065	

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

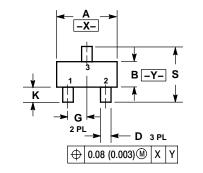
**SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

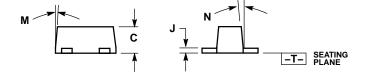
SC-89 CASE 463C-03 ISSUE C



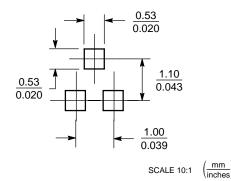
NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS
- 2
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS 3. IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 463C-01 OBSOLETE, NEW STANDARD 463C-02. 4.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.50	1.60	1.70	0.059	0.063	0.067	
в	0.75	0.85	0.95	0.030	0.034	0.040	
С	0.60	0.70	0.80	0.024	0.028	0.031	
D	0.23	0.28	0.33	0.009	0.011	0.013	
G	0.50 BSC			0.020 BSC			
н	C	).53 REF	-	0.021 REF			
J	0.10	0.15	0.20	0.004	0.006	0.008	
ĸ	0.30	0.40	0.50	0.012	0.016	0.020	
L	1	1.10 REF			0.043 REF		
М			10 °			10 °	
Ν			10 °			10 °	
S	1.50	1.60	1.70	0.059	0.063	0.067	



#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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